MMBT3906

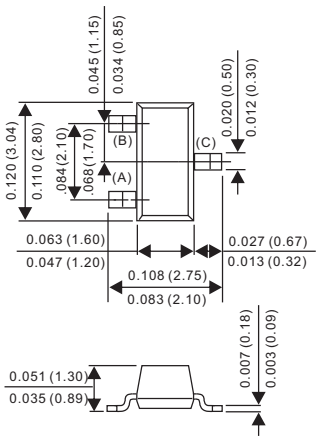
200mA Silicon PNP Epitaxial Planar Transistor

Features

- High collector-emitterbreakdien voltage. (BV_{CEO} -40V Min.@I_C=-1.0mA)
- Small load switch transistor with high gain and low stauration voltage, is designed for general purpose amflifier and switching applications at collector current.
- As complementary type, the NPN transistor FMBT3904 is recommended
- Capable of 225mW power dissipation.
- Lead-free parts for green partner, exceeds environmental standards of MIL-STD-19500 /228
- Compliant to Halogen-free

Package outline

SOT-23



Dimensions in inches and (millimeters)

Mechanical data

- Epoxy:UL94-V0 rated flame retardant
- Case : Molded plastic, SOT-23
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any

Maximum ratings (AT T_A=25°C unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Collector-base voltage		V_{CBO}			-40	V
Collector-emitter voltage		V_{CEO}			-40	V
Emitter-base voltage		V_{EBO}			-5.0	V
Collector current - continuous		I_C			-200	mA
Total device dissipation FR-5 board (Note 1)	T_A = 25°C	P_D			225	mW
	Derate above 25°C				1.8	mW/°C
Thermal resistance(Note 1)	Junction to ambient	$R_{\theta JA}$			556	°C/W
Thermal resistance(Note 1)	Junction to case	$R_{\theta JC}$			300	°C/W
Total device dissipation alumina substrate(Note 2)	T_A = 25°C	P_D			300	mW
	Derate above 25°C				2.4	mW/°C
Thermal resistance(Note 2)	Junction to ambient	$R_{\theta JA}$			417	°C/W
Thermal resistance(Note 2)	Junction to case	$R_{\theta JC}$			225	°C/W
Operating junction temperature range		T_J	-55		+150	°C
Storage temperature range		T_{STG}	-55		+150	°C

Notes 1: FR-5 = 1.0 X 0.75 X0.062 in.
2: Alumina = 0.4 X 0.3 X 0.024 in. 99.5% alumina.

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Electrical characteristics (AT T_A=25°C unless otherwise noted)

Off characteristics

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Collector-base breakdown voltage	I_C = -10uA, I_E = 0	$V_{(BR)CBO}$	-40			V
Collector-emitter breakdown voltage	I_C = -1mA, I_B = 0	$V_{(BR)CEO}$	-40			V
Emitter-base breakdown voltage	I_E = -10uA, I_C = 0	$V_{(BR)EBO}$	-5.0			V
Base cutoff current	V_{CE} = -30V, V_{EB} = -3.0V	I_{BL}			-50	nA
Collector cutoff current	V_{CE} = -30V, V_{EB} = -3.0V	I_{CEX}			-50	nA

On characteristics

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
DC current gain	I_c = -0.1mA, V_{CE} = -1.0V	h_{FE}	60			-
	I_c = -1.0mA, V_{CE} = -1.0V		80			
	I_c = -10mA, V_{CE} = -1.0V		100		300	
	I_c = -50mA, V_{CE} = -1.0V		60			
	I_c = -100mA, V_{CE} = -1.0V		30			
Collector-emitter saturation voltage(1)	I_c = -10mA, I_B = -1.0mA	$V_{CE(sat)}$			-0.25	V
	I_c = -50mA, I_B = -5.0mA				-0.40	
Base-emitter saturation voltage	I_c = -10mA, I_B = -1.0mA	$V_{BE(sat)}$	-0.65		-0.85	V
	I_c = -50mA, I_B = -5.0mA				-0.95	

1.Pulse test : pulse width≦300us, duty cycle ≦2.0%.

Small-signal characteristics

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Current-gain-bandwidth product	I_C = -10mA, V_{CE} = -20V, f = 100MHz	f_T	250			MHz
Output capacitance	V_{CB} = -5.0V, I_E = 0, f = 1.0MHz	C_{obo}			4.5	pF
Input capacitance	V_{EB} = -0.5V, I_C = 0, f = 1.0MHz	C_{ibo}			10	pF
Input impedance	V_{CE} = -10V, I_C = -1.0mA, f = 1.0KHz	h_{ie}	2.0		12	kohms
Voltage feeback radio	V_{CE} = -10V, I_C = -1.0mA, f = 1.0KHz	h_{re}	0.1		10.0	X 10^{-4}
Small-signal current gain	V_{CE} = -10V, I_C = -1.0mA, f = 1.0KHz	h_{fe}	100		400	-
Output admittance	V_{CE} = -10V, I_C = -1.0mA, f = 1.0KHz	h_{oe}	3.0		60	μmhos
Noise figure	V_{CE} = -5.0V, I_C = -100uA, Rs = 1.0K ohms, f = 1.0KHZ	NF			4.0	dB

Switching characteristics

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Delay time	V_{CC} = -3.0V, V_{BE} = 0.5V, I_C = -10mA, I_{B1} = -1.0mA	td			35	ns
Rise time		tr			35	
Storage time	V_{CC} = -3.0V, I_C =-10mA, I_{B1} = I_{B2} = -1.0mA	ts			225	
Fall time		tf			75	

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Switching time equivalent test circuits

Figure 1. Delay and Rise Time Equivalent Test Circuit

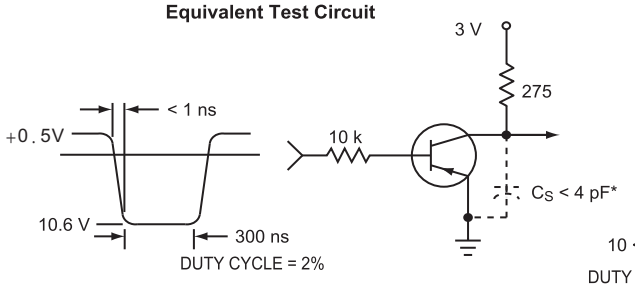
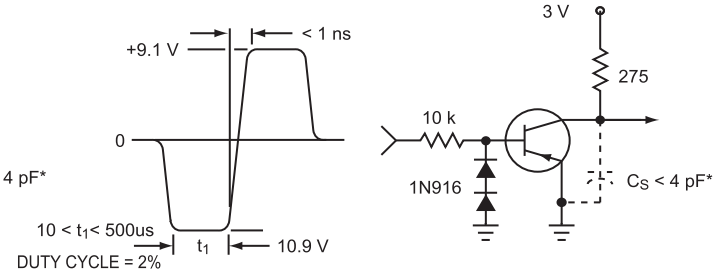


Figure 2. Storage and Fall Time Equivalent Test Circuit



* Total shunt capacitance of test jig and connectors

TYPICAL TRANSIENT CHARACTERISTICS

Figure 3. Capacitance

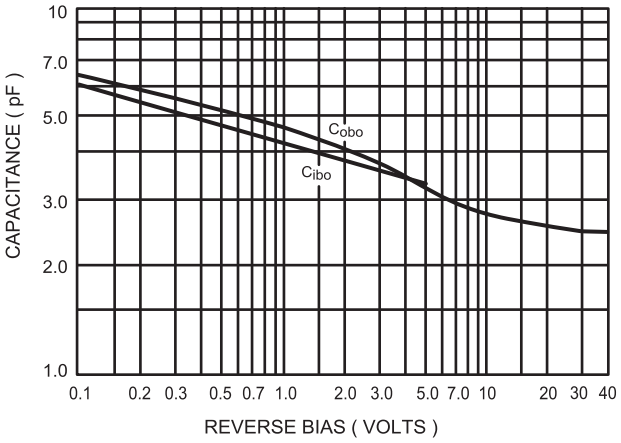


Figure 4. Charge Data

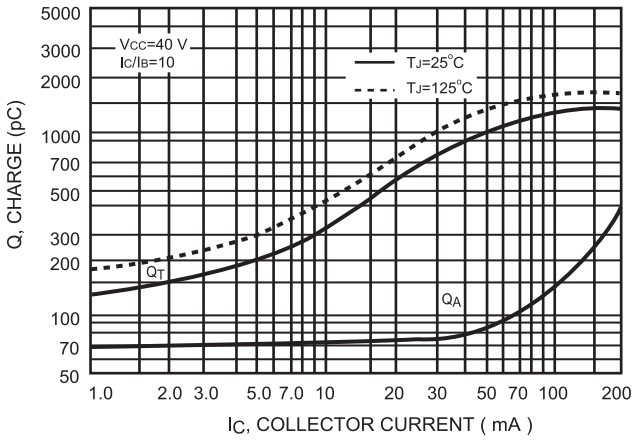


Figure 5. Turn-On Time

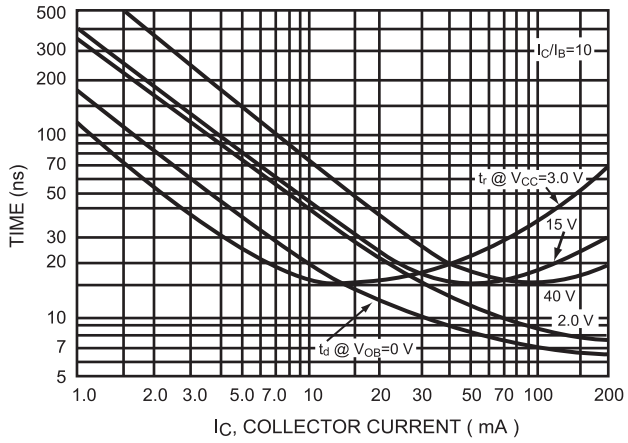
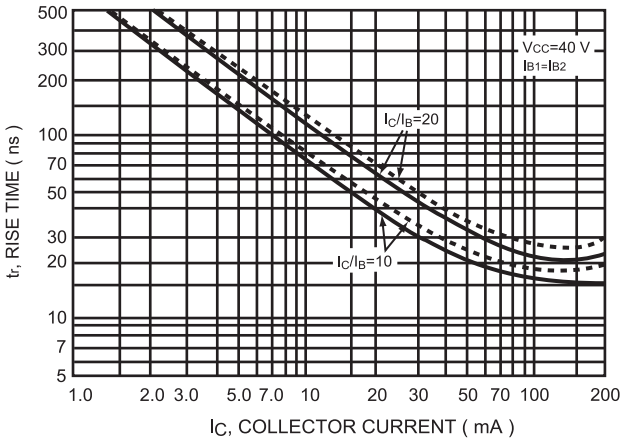


Figure 6. Fall Time



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TYPICAL TRANSIENT CHARACTERISTICS

NOISE FIGURE VARIATIONS

(V_{CE}= -5.0Vdc, T_A=25°C, Bandwidth=1.0Hz)

Figure 7.

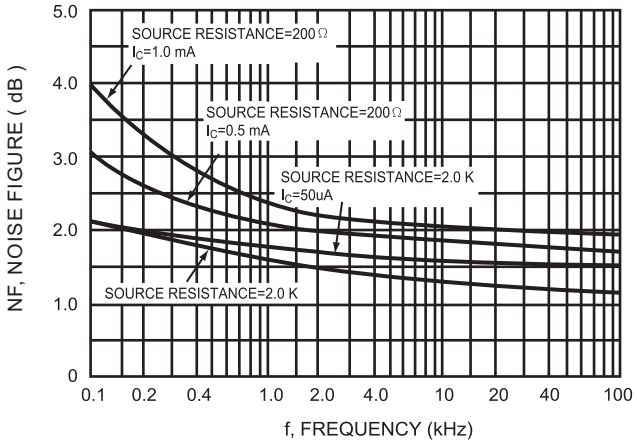
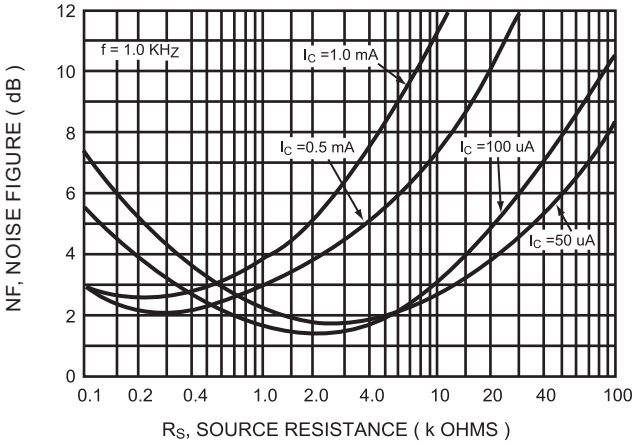


Figure 8.



h PARAMETERS

(V_{CE}= -10Vdc, f=1.0 kHz, T_A=25°C)

Figure 9. Current Gain

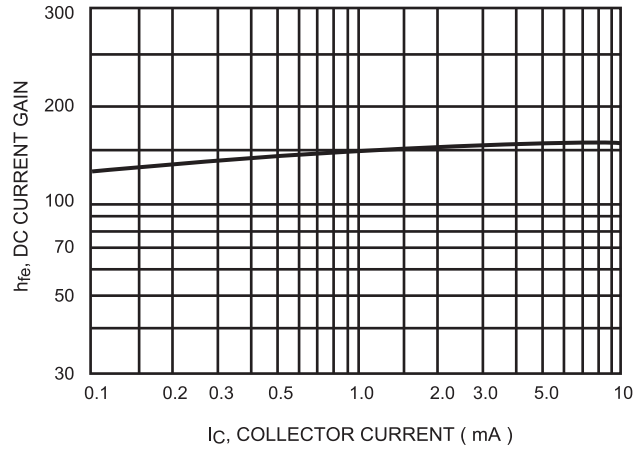


Figure 10. Output Admittance

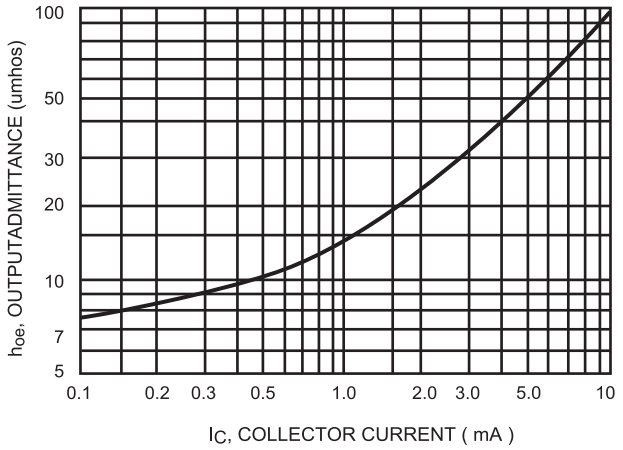


Figure 11. Input Impedance

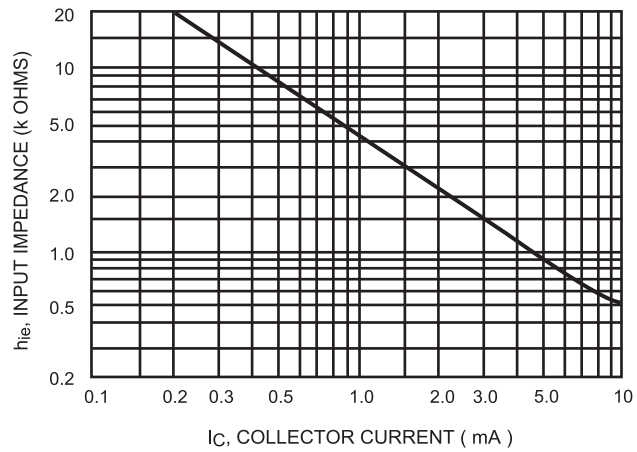
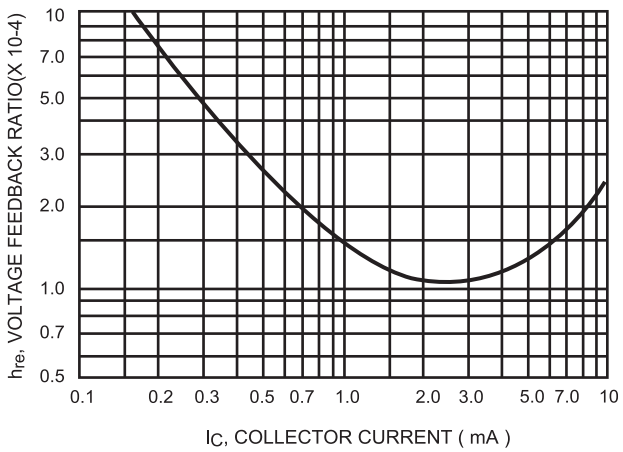


Figure 12. Voltage Feedback Ratio



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TYPICAL STATIC CHARACTERISTICS

Figure 13. DC Current Gain

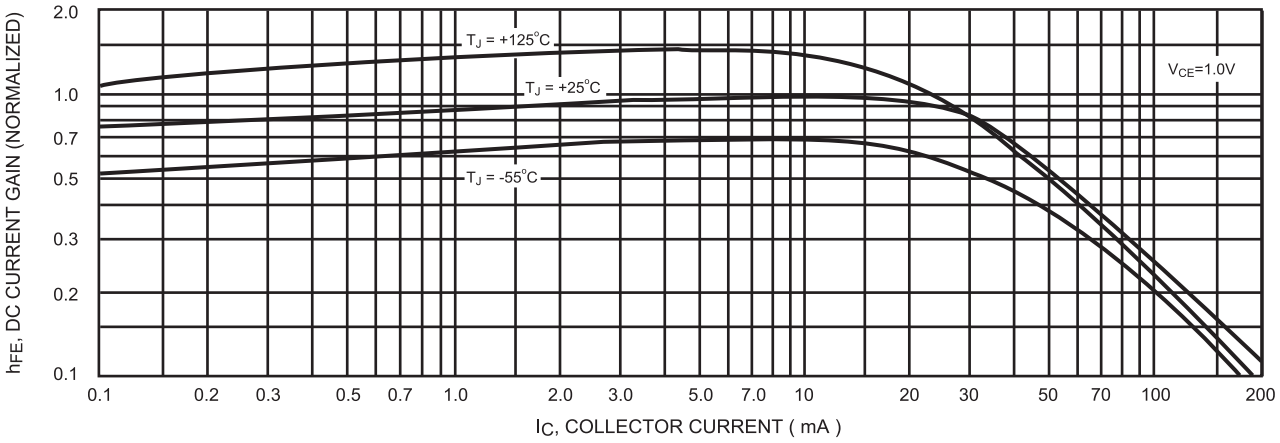


Figure 14. Collector Saturation Region

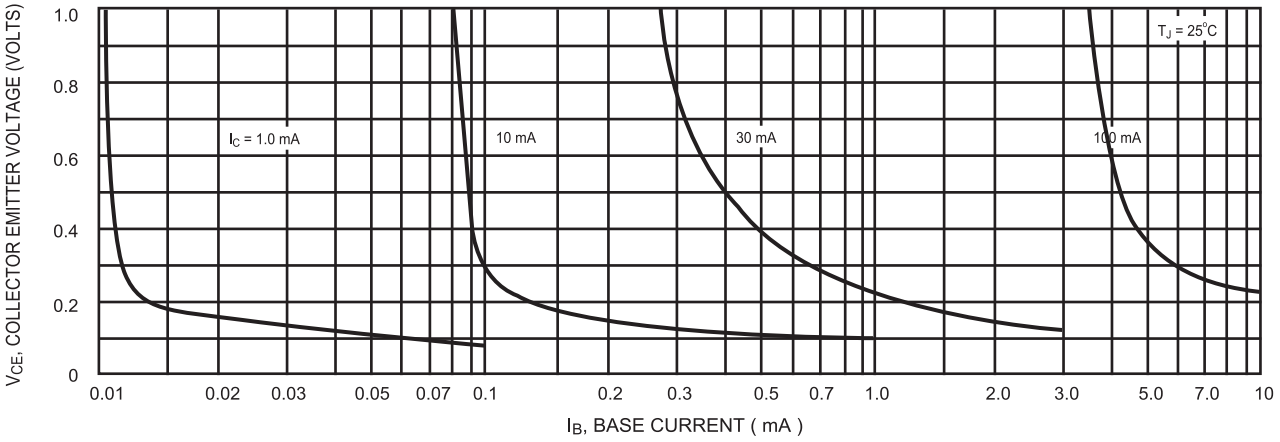


Figure 17. " ON " Voltage

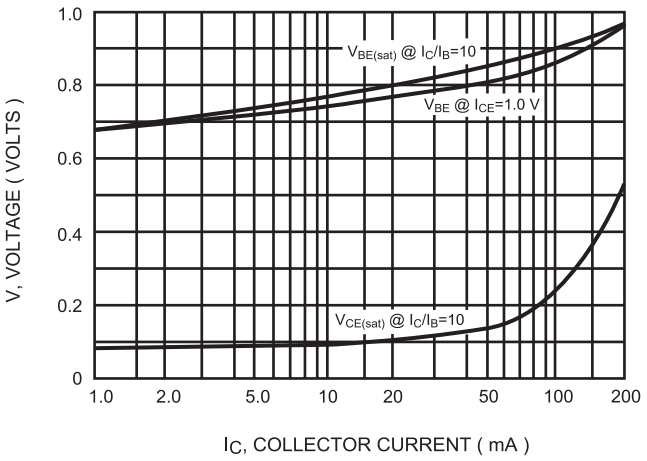
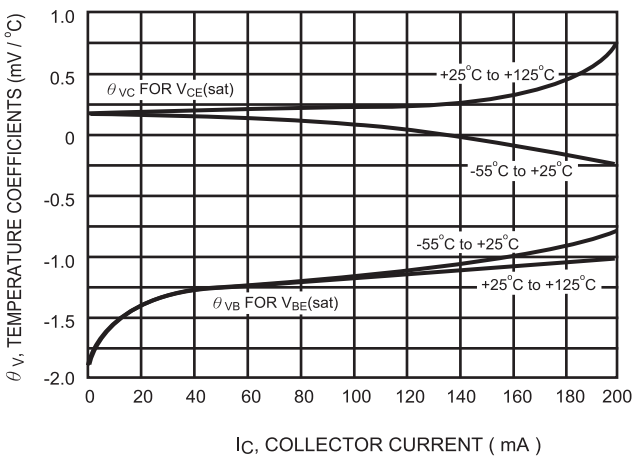


Figure 16. Temperature Coefficients



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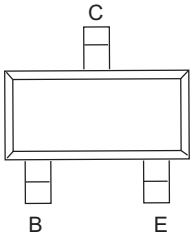
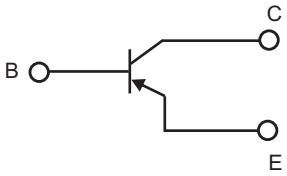
Pinning information

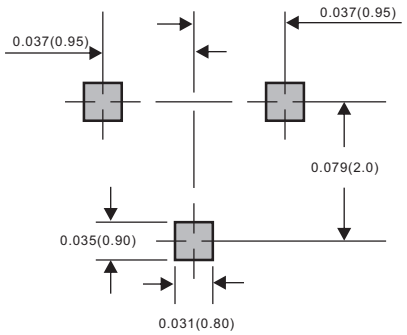
Pin	Simplified outline	Symbol
PinB Base PinC Collector PinE Emitter		

Marking

Type number	Marking code
MMBT3906	2A

Suggested solder pad layout

SOT-23



Dimensions in inches and (millimeters)